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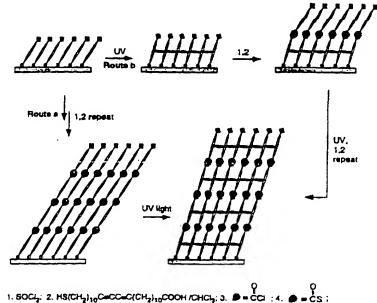
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(57) Abstract

A self-assembled multilayer and in particular polymeric self-assembled multilayer can be effectively produced from two or more selfassembled monolayers on a substrate where each of the self-assembled monolayers is produced for a block containing a first functional group and a second functional group where the second functional group is reacted with the first functional group. The production of polymerizable, self-assembled mono- and multilayers from, e.g., blocs containing at least two acetylene groups and/or polymerizable end groups, is also provided. The polymerized mono- or multilayer can be employed in a variety of applications including photolithography.



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TITLE OF THE INVENTION

Polymeric Self-Assembled Mono- and Multilayers and Their Use in Photolithography

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Field of the Invention

The present invention relates to self-assembled monoand multilayers and, in particular, polymeric selfassembled mono- and multilayers as well as the use of 10 self-assembled mono- and multilayers in certain applications such as photolithography.

Background of the Invention

Self-assembled monolayers (SAMs) are known in the art. See, for example, Dubois et al., Annu. Rev. Phys.

- 15 Chem., 1992, 43, p. 437 et seg., which is incorporated herein by reference. Recently, one class of SAM that has received considerable attention are organomercaptans. See, for example, Kim et al. "Polymeric Self-Assembling Monolayer. 1. Synthesis and Characterization of ω -
- 20 Functionalized N-Alkanethiol Containing a Conjugated Diacetylene Group" Tetrahedron Letters, Vol. , No. 51, pp. 9501-9504, 1994; Kim et al., "Polymeric Self-Assembling Monolayer. 2. Synthesis and Characterization of Self-Assembled Polydiacetylene Mono- and
- 25 Multilayers.", J. Am. Chem. Soc., 1995, 117, pp. 3963-3967; and Batchelder et al., "Self-Assembled Monolayer containing Polydiacetylenes", J. Am. Chem. Sc., 1994, 116, pp. 1050-1053, each of which are incorporated herein by reference in their entirety.
- One area of study relating to SAMs has involved the stability of such monolayers. While in certain environments, e.g., water or air at room temperature, the SAM's can be considered robust, one disadvantage associated with the use of most SAMs relates to their

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fragility in environments that involve elevated temperatures and/or solvents able to penetrate the SAM.

One solution to this problem is represented by the polymerization of SAMs. Batchelder et al disclose the use of UV radiation in polymerizing SAMs produced from methyl-terminated diacetylene disulfide. While it has been found that polymerized SAMs have high structural integrity and are more rugged than their unpolymerized counterparts, SAMs produced from methyl-terminated diacetylene disulfide are very limited in their use. Because of the presence of the methyl group at the terminal end of the SAM blocks, the surface of the SAM

In a different vein, the art has looked at

15 multilayer assemblies of self-assembling monolayers. For example, the formation of built up films by the stepwise adsorption of individual monolayers is described in U.S.

Patent No. 4,539,061 to Sagiv. However, these monolayers suffer from the same disadvantages as other non-

according to Batchelder is considered nonreactive.

20 polymerized monolayers. Moreover, the process described in this patent itself is limiting. That is, the process requires the use of a molecule having a polar "head" and a non-polar functional group in producing the monolayer. This is followed by a conversion of non-polar groups to a polar head in order to allow for the build up of

subsequent monolayers. Accordingly, not only is the disclosed process relatively complex but the practical applications are limited.

Accordingly, the need still exists for an improved 30 polymeric self-assembled mono- and multi-layer structure that does not suffer from the limitations associated with previous films.

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Summary of the Invention

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Surprisingly, it has been found that certain self-assembled monolayers are capable of being formed into self-assembled multilayers, and, in particular, polymeric self-assembled multilayers. Moreover, the polymeric self-assembled mono- and multi-layers described herein have a combination of properties which allows them to be employed in a wide variety of applications such as adhesion layers and lithographic resists.

In one aspect the present invention relates to a
self-assembled multi-layer structure comprising a
substrate and a plurality of self-assembled monolayers,
with each of said self-assembled monolayers being
produced from a block containing a first functional group
and a second functional group reacted with the first
functional group. In one particular preferred
embodiment, the first functional group is a thiol group,
the second functional group is a carboxylic acid group,
hydroxyl group or an epoxy group. Moreover, at least
one of the self-assembled monolayers are polymerized,
e.g., produced from a compound containing at least one
pair of conjugated acetylene bonds and/or a polymerizable
end group and then polymerized.

In another aspect of the invention, a method of photolithography is provided. This method includes

25 providing a support having at least one self-assembled monolayer thereon, said self-assembled monolayers produced from a molecule including at least two acetylene bonds, introducing a mask onto self-assembled monolayer in a desired pattern inducing the polymerization of the unmasked regions of the self-assembled in a plane roughly parallel to the substrate in removing the unpolymerized portion of the self-assembled monolayers. The method can further include

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etching of the substrate surface subsequent thereto or deposition of an inorganic or organic material thereon.

Brief Description of the Drawing

Figure 1 illustrates a synthesis method for producing diacetylenic thiols which can be employed in the present invention;

Figure 2 illustrates a method for forming a polymeric self-assembled mono- or multilayer;

Figure 3 illustrates a method of photolithography 10 according to the present invention;

Figures 4-7 illustrate properties of polymeric multilayers;

Figure 8 are micrographs relating to the exemplified method of photolithography; and

15 Figure 9a is a three dimensional STM image of a pattern Au surface and Figure 9b is a depth profile on the line of Figure 9a.

Description of the Preferred Embodiments

The self-assembled monolayers employed in the
present invention are produced from molecules or blocks
that include at least two functional groups, i.e., a
first functional group capable of being attached to a
surface, and a second functional group which is capable
of being covalently bonded with the first functional
group of another molecule or block. The use of blocks

25 group of another molecule or block. The use of blocks having such a combination of functional groups allows for the sequential buildup of monolayers on a surface.

Examples of suitable first functional groups include thiol groups, carboxylic acids and silanes, with thiols being preferred.

The selection of suitable second functional groups is dependent, of course, on the first functional group employed. For example, preferred second functional groups for use where the first functional group is a

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thiol include carboxylic acid groups, hydroxy groups, and epoxy groups.

As discussed above, it is also desirable that the SAM be polymerizable. While the various applications associated with the present invention can utilize SAMs polymerized by any known technique, the following two methods are discussed herein.

In one embodiment for providing a polymerizable SAM, it is desired that the self-assembled monolayers be produced from molecule or blocks containing at least one pair of conjugated acetylene bonds. While the conjugated bonds can be placed at any suitable location in the block, near or at the center of the molecule is preferred. By center it is meant that there are about the same number of carbon atoms on both sides of the conjugated bonds. SAMs produced from such blocks are typically polymerized by irradiation, e.g., UV, visible light, infrared, x-rays, and the like with UV irradiation being preferred.

Another method of providing a polymerizable SAM involves the use of polymerizable second functional or end groups. Examples of such groups, which can be polymerized through irradiation or electrochemistry, include aniline groups, thiophene groups and pyrrole groups.

Combinations of the foregoing could also be employed. For example, a multi-layer including one or more monolayers produced from blocks with conjugated acetylene bonds and one or more layers produced from compounds having polymerizable end groups. Moreover, blocks containing both conjugated acetylenic groups and polymerizable end groups can be employed.

The use of SAMs produced from conjugated acetylene bonds is preferred due to the fact that the 35 polymerization

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of SAMs with polymerizable end groups results in a material that is not further reactive. That is, by polymerizing the end groups further reaction of the SAM is not possible.

- Preferred examples of suitable blocks for forming the monolayers include organomercaptans such as diacetylenic thiols, e.g., ω-functionalized n-alkanethiols. The compounds preferably have from 4-40 carbon atoms, more preferably 20-30, and still more preferably about 25 carbon atoms. Specific examples
- preferably about 25 carbon atoms. Specific examples of suitable compounds include ω -functionalized nalkanethiols containing a diacetylene group such as $HS(CH_2)_{10}C\equiv CC\equiv C(CH_2)_{10}COOH$ and $HS(CH_2)_{10}C\equiv CC\equiv C(CH_2)_{10}OH$.
- Methods for producing SAMs in which the desired

 15 functional groups disclosed in the two Kim et al.

 articles discussed above and thus need not be described

 in detail here. However, for sake of completeness,

 Figure 1 illustrates a suitable synthesis technique. As

 illustrated in this figure, the synthesis of diacetylene-
- containing alkanethiols includes the selective deprotection of 1,4-bis(trimethylsilyl)-1,3-butadiyne (1 of Fig. 1), subsequent reaction with primary alkylbromides and deprotection of the remaining trimethylsilyl group. The lithium diacetylenide (2 of
- 25 Figure 1) can then be reacted with 1,10-dibromodecane to give a functionalized alkylbromide (3 of Figure 1).

 Oxidation of the alkylbromide provided a diacetylene (5 of Figure 1) that is then converted to the corresponding thiols (6,7 of Figure 1).
- Where conjugated acetylenic bonds are employed, polymerization of the SAMs in a plane which is roughly parallel to the surface of the substrate can be performed through irradiation with, e.g., visible light, infrared, x-ray or UV radiation, with UV being preferred. See, for example, the discussion in the two Kim et al. articles

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and the Batchelder et al. article. As discussed above, the use of polymerizable end groups allows for polymerization through electrochemical techniques that are also recognized in the art.

Multilayers assemblies of self-assembled monolayers are produced through the sequential deposition of a plurality of SAMs (Figure 2).

In particular, the individual monolayers are covalently bonded to the immediate preceding layer

10 through the reaction of the second functional group of a first block with the first functional group of a second block. For example, where the second functional group is a carboxylic acid and the first functional group is a thiol, the acid is converted to an acid chloride and the layers are then covalently bonded through a thioester linkage. The conditions associated with such processes would be well within the purview of those skilled in the art.

Moreover, other suitable combinations of

20 functional groups capable of providing a covalent bond
between the individual layers would also become apparent
to hose skilled in the art and can also be employed.

Polymeric multilayers according to the present invention are preferably produced by either of two synthesis routes illustrated in Figure 2. Although the following discussion with focus on the preferred use of the carboxylic acid-terminated alkanethiol diacetylene HS(CH₂)₁₀C=CC=C(CH₂)₁₀COOH, it should not be limited to that particular molecule.

In general, synthesis Route a illustrates the ability to provide an assembled multilayer in which the assembly of individual monolayers is provided and are polymerized during production of the multilayer but, which subsequent to polymerization, each layer is polymerized.

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Alternatively, Route b illustrates a synthesis method by which each layer is polymerized as it is introduced onto the previous layer.

As can be seen, both routes involve the same

5 process for introducing the SAM onto the substrate or the
previous SAM layer, i.e., converting the carboxylic acid
terminal groups to an acid chloride by exposure to SOCl,
vapor followed by subsequent reaction with the desired
block. The significant difference between the two routes

10 is the timing of the irradiation, i.e., either once after
depositing all of the SAMs or after the deposition of
each SAM.

The present invention is therefore capable of providing an arrangement exists where all of the layers are polymerized or, where one or more of the outermost layers may not be polymerized with the balance of the layers being polymerized.

Surprisingly, not only are the polymerized SAMs are extremely rugged, they are better barriers to 20 transfilm mass transfer than unpolymerized monolayers. Accordingly, it has been discovered that the selfassembled mono- and multilayers according to the present invention can be employed as an adhesion layer in a variety of environments. One such area is as adhesion 25 layers. Adhesion layers are, in general, known in the art and can be employed in a number of different environment. Such layers can allow the formation of composite materials which are otherwise difficult, if not impossible, to provide. For example, merely introducing 30 a layer of gold onto silicon is ineffective due to poor compatibility, and the gold will peel off in a matter of days. On the other hand, through the use of a suitable adhesion layer, e.g., chromium, which is capable of bonding to both the gold and the silicon, suitable 35 composites can be provided.

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Here, self-assembled mono- and multilayers and in particular, polymerized mono- and multilayers according to the present invention can be employed as adhesion layers in a variety of environments. First of all, the sability of SAMs to bond to a variety of substrates under a wide range of conditions, e.g., temperatures less than about 400 C, makes their use attractive in this context. Moreover, as discussed above, once polymerized, the SAMs are stronger, more resistant to degradation, and thus, tan provide even better adhesion.

Specific examples of suitable substrates include gold, aluminum, aluminum oxide, gallium-arsenide, copper and silver.

Moreover, upon introduction of a self-assembled

15 mono- or multilayer onto a substrate, additional outer
layers can be provided. Such additional layers are
limited only by their ability to react with the second
functional group of the SAM and the intended final use
for the composites. Specific examples of such "outer

20 layers" include chemically sensitive organic and
inorganic materials, metals and semiconductors to name a

The multilayer assemblies according to the present invention are capable of providing additional advantages.

In this regard, a polymerized multilayer provides a highly structured three-dimensional, surface-confined polymer which can be employed as, e.g., ordered conductive polymers, third-order nonlinear optical materials and, one particularly preferred embodiment,

30 lithographic resists.

few.

A method for using self-assembled mono- and multilayers as a photoresist and, in particular, a negative photoresist, is illustrated by Figure 3.

This aspect of the invention involves the use of a 35 self assembled mon- or multilayer and the introduction of

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a suitable mask in a desired pattern onto the surface of the mono- or multilayer. The self-assembled monolayer is then irradiated with UV radiation, so as to induce polymerization in the unmasked regions of the mono- or multi-layer.

The unpolymerized portion of the resist is then selectively desorbed using a suitable electrochemical reductive stripping method which results in a negative image of the mask. Selective stripping can be

10 effectively employed in this process because the polymeric mono- or multilayers are sufficiently insoluble in the stripping agent and strongly bond to the surface that only the monomeric SAMs are removed. Finally, suitable processing, e.g., etching can be preformed to

15 elaborate on the negative image of the mask in providing the desired resist. Alternatively, this can involve deposition of an inorganic or organic material thereon.

The individual steps discussed above, e.g., selective stripping, etching, depositions and the like, 20 can be performed with traditional materials and by traditional techniques. In fact, the ability to readily and easily "plug" the resists of the present invention into existing processes without the costs in both time and money associated with retrofitting or redesigning is 25 a significant advantage of the inventive process.

Moreover, because the use of self-assembled monoor multilayer consist of single small molecules or very thin layers of molecules, the theoretical resolution of lithography is the graphically defined features can be as 30 small as a few (e.g., less than 10) nanometers when patterned by an appropriate tool, e.g., the tip of scanning tunnel microscope.

SAMs are extremely dense and, in some cases the structure approaches that of a two-dimensional crystal.

This ensures high effective density and simplifies resist

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application and stripping. In fact, the use of stripping solutions can be greatly minimized or eliminated. The environmental impact of that advantage in terms of eliminating the need to process or dispose such solution 5 can not be understated.

Finally, insofar as the terminal group, i.e., second functional group, of the SAMs can be varied, selective chemicals physical vapor definition of materials can be enhanced.

The present invention will now be described in terms of certain preferred examples thereof. However, these examples are intended to be illustrative in nature and should, in no way, limit the present invention.

Example 1

Gold substrates for FTIR-external reflectance spectroscopy (FTIR-ERS), ellipsometry, and Raman spectroscopy were prepared by thermal evaporation of 2000 Å of Au over a 50-Å Cr adhesion layer confined to Si(100). For UV-vis measurements, transparent substrates were prepared by thermal deposition of 50 Å of Au onto a (3-mercaptopropyl)trimethoxysilane adhesion layer confined to a quartz substrate. The substrates were cleaned in piranha solution (30% H₂O₂:concentrated H₂SO₄ = 1:3)

Monolayers were prepared by soaking the substrate in a 1 mM CHCl₃ solution of HS(CH₂)₁₀C≡CC≡C(CH₂)₁₀COOH for 1 h, removing the substrate, and then rinsing it in acetone and deionized water. Multilayers were prepared by thioester coupling of HS(CH₂)₁₀C≡CC≡C(CH₂)₁₀COOH to the base monolayer either before or after polymerization of the base layer. The carboxylic acid-terminated SAM was positioned in a closed container, and after the container was purged with dry N₂ for 5 min, SOCl₂ vapor was introduced for 10 min. Control experiments, which

the state of the strainers

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involved monitoring this reaction by FTIR-external reflectance spectroscopy in real time, indicated that the absorbance due to the carboxylic acid carbonyl stretching mode originally present around 1713 cm⁻¹ was completely eliminated within 1 min and replaced by an absorbance at 1813 cm⁻¹ that we identify as the acid chloride carbonyl mode. The substrate was then transferred to a 1 mM CHCl₃ solution of HS(CH₂)₁₀C=CC=C(CH₂)₁₀COOH, and thioester formation was complete with 1 h. Subsequent layers were prepared similarly.

Except for the UV-vis spectroscopic experiments, polymerization was performed by placing the substrate into a gas-tight container and irradiating it under a N_2 purge for 5 min with a lamp (Oriel, Model 6035) 15 positioned 1 cm above the substrate.

FTIR-ERS measurements were made using a Digilab FTS-40 FTIR spectrometer equipped with a Harrick Scientific Seagull reflection accessory and a liquid N_2 -cooled MCT detector. All spectra were obtained using p-20 polarized light incident on the Au substrate at an angle of 84°.

Thickness measurements of the unpolymerized monoand multi-layers were made using a Gaertner Scientific ellipsometer (Model L116C). The data were obtained using 25 the 488 nm Ar laser line, but the 633 nm He-Ne laser line yielded similar results. A refractive index of 1.46 was assumed for the thickness calculations. Due to optical absorptions it was not possible to measure the thickness of the polymerized multilayer SAMs using ellipsometry.

The UV-vis spectra were recorded on a Hewlett-Packard diode-array spectrometer by first obtaining a background spectrum of a four-layer, unpolymerized film, and then polymerizing it for various lengths of time without removing the substrate from the spectrometer (in 35 these experiments the UV light was maintained 0.5-1.0 cm

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away from the substrate). Throughout these experiments the substrate was kept under a N_2 purge.

The Raman measurement system consists of a Kr-ion laser (Model Innova 90K, Coherent Laser Group, Santa 5 Clara, CA), a 3-in.-diameter holographic notch filter (Model Notch-Plus, Kaiser Optical System, Ann Arbor, MI), 0.5-m single-grating Czerny-Turner spectrograph (Model 500M, SPEX Industries, Edison, NJ), a liquid- N_2 -cooled 1024-by-26-pixel charge-coupled device (CCD) (Model CCD-10 1000LF, SPEX Industries). Laser power was measured by a semiconductor detector (Model 840-C and 818-SL/CM, Newport, Irvine, CA). The spectral position, of the horizontal CCD pixels were calibrated using emission lines of known wavelengths from a Ne lamp (Model AlA/NE-15 2, Chicago Miniature Lamp, Buffalo, IL). Typical conditions for Raman scattering were 5 mW 647.1 nm excitation 200 mm slit width (equivalent to 6.7 cm⁻¹ band pass), and 5 s integration time. The spectra were corrected for a slowly varying spectral background using 20 set points more than 200 cm⁻¹ apart. The laser was focused to a point on the sample surface using a $f=250~\mathrm{mm}$ spherical focusing lens.

Figure 4 shows FTIR-ERS spectra of

HS(CH₂)₁₀C≡CC≡C(CH₂)₁₀COOH obtained after each of five

25 incremental increases in layer thickness and subsequent polymerization immediately following the addition of each layer (Route b). Figure 4-a corresponds to a single, polymerized monolayer of HS(CH₂)₁₀C≡CC≡C(CH₂)₁₀COOH. The spectrum is composed of three prominent peaks: methylene asymmetric and symmetric C-H stretches at 2926 and 2854 cm⁻¹, respectively, and the carboxylic acid CDO stretch at 1713 cm⁻¹. The positions of the methylene bands are in general agreement with previous studies, and they indicate that the hydrocarbon portions of the chains probably exist in a liquid-like state. As discussed

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later, the absorbance of the methylene bands in the second and subsequent layers is greatly attenuated following polymerization due to a change in orientation of the hydrocarbon backbone relative to the Au substrate.

5 After obtaining the spectrum in Figure 4a, we reacted the terminal acid groups with SOCl, to convert them to the acid chloride, which reacts with HS(CH₂)₁₀C≡CC≡C(CH₂)₁₀COOH to form a thioester-bound bilayer. Exposure to UV light polymerizes the second 10 layer. Figure 4b shows that this treatment increases the absorbance due to both the methylene and carbonyl groups. The methylene band intensity increased by about 30% which is consistent with subsequent layering steps (Figure 4c, d, e), which show the same incremental increase in 15 absorbance observed for the second layer (inset of Figure 4). From these data we conclude that the first polymerized layer is significantly tilted with respect to the surface normal, perhaps as much as 35° based on the ellipsometric data discussed later, but subsequent 20 polymerized layers are oriented more perpendicular to the surface-perhaps about 20° from the surface normal based

on ellipsometry data and the difference in the maximum IR

absorbance.

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25 backbone upon polymerization is confirmed by Figure 5.
Figure 5a, which is the same as Figure 4c, is a spectrum of a three-layer polydiacetylene film. Figure 5b is the spectrum that results from coupling a fourth unpolymerized layer to the multilayer of Figure 5a. The large change in absorbance in the hydrocarbon region is consistent with the addition of the fourth layer.

However, upon polymerization (Figure 5c) the magnitude of these peaks decreases significantly. This result suggests that the methylene bonds are oriented more

- 15 -

parallel to the substrate after polymerization and confirms the structural change mentioned earlier.

Figure 6 also shows in situ UV-vis transmission spectra as a function of polymerization time for a 45 layer film made according to Route a (Figure 2). The data indicate that polymerization is complete within 5 min. Exposure of the film to UV light for times up to 8 min revealed no further change in the intensity or position of the absorption maximum, which occurs at 620 nm. In studies of polydiacetylene Langmuir-Blodgett films, two absorption maxima are usually observed. One is found between 600 and 640 nm, which corresponds to the so-called blue polymer, and the other is between 500 and 550 nm, which corresponds to the shorter or less
15 conjugated red polymer. The self-assembly approach yielded only the more highly conjugated blue polymer.

The surface Raman spectrum of the same substrate used to obtain the data shown in Figure 4 confirms polymerization (Figure 7). Three major peaks located at 20 687, 1444, and 2072 cm⁻¹ all originate from vibrations of the polydiacetylene backbone, which contains conjugated and alternating double and triple bonds. The peak at 687 cm⁻¹ has previously been assigned to a bending mode of the backbone, and peaks at 1444 and 2072 cm⁻¹ correspond
25 mainly to the C=C and C=C stretching vibrations, respectively. These frequencies are significantly lower than those observed for isolated C=C and C=C stretching modes (approximately 1620 and 2260 cm⁻¹, respectively). The decrease in both frequencies is due to extensive electronic delocalization in the backbone of the polymerized diacetylene groups.

Example 2

A diacetylenic SAM was used as a negative photoresist and the image of a transmission electron

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microscope (TEM) minigrid was transferred into a Au substrate using the three steps illustrated in Figure 3.

First, the minigrid was placed in contact with a SAM composed of close-packed $HS-(CH_2)_{10}C\equiv CC\equiv C(CH_2)_{10}COOH$ 5 molecules confined to a Au/Cr/Si surface. The entire assembly was then exposed to UV light, which induced polymerization in the unmasked regions of the SAM (B-Figure 3). Next the unpolymerized portion of the resist was selectively desorbed using an electrochemical 10 reductive stripping method (C-Figure 3). Selective stripping was possible because the polymeric SAM is sufficiently insoluble and strongly bound to the surface through multiple Au/S and van der Waals interactions that it survives potential excursions that remove monomeric 15 organomercaptan SAMs. Resist removal resulted in a negative image of the mask, which can be elaborated by etching the grid image into the Au surface with an O,saturated 1 M KOH plus 10 mM KCN aqueous solution (D-Figure 3).

Figure 8a is an optical micrograph of the 400-mesh (holes per linear inch) Cu TEM minigrid, which was used to pattern the Au surface. Panels b and c of Figure 8 are scanning electron micrographs (SEMs) of a patterned Au surface, such as that illustrated in Figure 3, frame D obtained at two different magnifications. At this level of resolution, an excellent reproduction of the mask features was observed.

Figure 9a is a three-dimensional STM image (90 μ m x 90 μ m) of the pattern shown in Figure 7b,c. The 30 grooves in this image are regions of the Au surface that have been etched by the KCN/KOH solution, while the hexagonal regions are those parts of the Au surface that etch at a reduced rate as a result of the presence of the

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polymeric SAM resist. STM depth profiles (Figure 9b) indicate the grooves were about 7-8 nm deep.

Although the present invention has been described in terms of certain preferred embodiments, those skilled in the art will recognize that various modifications, omissions, substitutions, and other changes can be made without departing from the spirit thereof. Thus, the scope of the present invention should be limited only by the scope of the following claims including equivalents thereof.

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What is claimed is:

- 1. A self-assembled multilayer structure comprising:
 - a substrate and
- a plurality of self-assembled monolayers deposited thereon, with each of said self-assembled monolayers being produced from a block containing a first functional group, a second functional group that is reactive with the first functional group, wherein at least one of the monolayers is polymerized in a plane roughly parallel to the substrate.
 - 2. The structure according to claim 1 where the first functional group is a thiol, carboxylic acid or silane group.
- 3. The structure according to claim 1 where the second functional group is a carboxylic acid group, hydroxy group, or epoxy group.
- The structure according to claim 1 wherein at least one of the self-assembled monolayers are produced
 from a compound further including at least one pair of conjugated acetylene bonds.
 - 5. The structure according to claim 4 wherein the compounds contains a pair of conjugated acetylene bonds in the center of the compound.
- 6. The structure according to claim 1 wherein at least one of the self-assembled monolayers is produced from a compound having a second functional group which is polymerizable.

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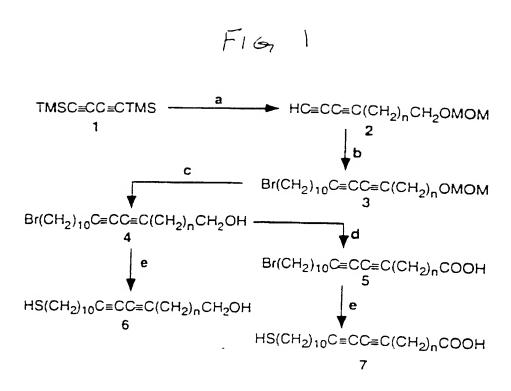
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- 7. The structure according to claim 1 wherein more than one of the self-assembled monolayers are polymerized in a plane roughly parallel to the substrate.
- 8. The structure according to claim 1 wherein 5 each of the self-assembled monolayers are polymerized in a plane parallel to the substrate.
 - 9. The structure according to claim 4 wherein the self-assembled monolayers are produced from organomercaptans.
- 10 10. In the structure according to claim 8 wherein the organomercaptans are diacetylenic thiols.
 - 11. The structure according to claim 8 wherein the organomercaptans are ω -functionalized diacetylenic nalkanethiol having 4-40 carbon atoms.
- 15 l2. The structure according to claim 10 wherein the diacetylenic thiol has the formula $\text{HS}(\text{CH}_2)_{10}\text{C} \equiv \text{CC} \equiv \text{C}(\text{CH}_2)_{10}\text{COOH or HS}(\text{CH}_2)_{10}\text{C} \equiv \text{CC} \equiv \text{C}(\text{CH}_2)_{10}\text{OH}.$
 - 13. A multilayer structure comprising: a substrate;
- an adhesion layer comprising at least one selfassembled monolayer bonded thereto; and at least one outer layer bonded to said adhesion layer, wherein said at least one outer layer is not compatible with said substrate.
- 25 14. The structure according to claim 13 wherein at least a portion of at least one of the self assembled monolayers is polymerized in a plane roughly parallel to the substrate.

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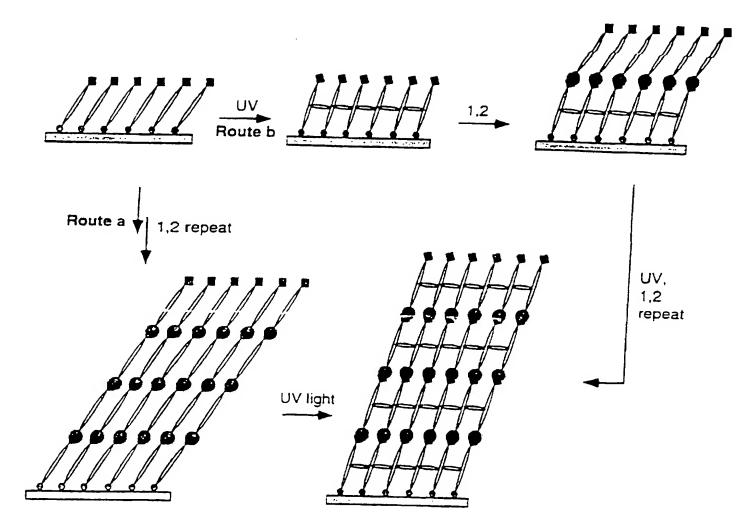
- 15. The structure according to claim 13 wherein at least one adhesion layer comprises a self-assembled monolayer which is polymerized in a plane roughly parallel to the substrate.
- 5 16. The structure according to claim 13 further comprises one or more additional layers between the substrate and the adhesion layer.
 - 17. A method for photolithography comprising:
- (a) providing a support having at least one self-10 assembled monolayer, said self-assembled monolayer being produced from a molecule including at least two acetylene bonds;
 - (b) introducing a mask onto said self-assembled monolayer in a desired pattern;
- 15 (c) inducing the polymerization of the unmasked regions of the self-assembled monolayer in a plane parallel to the substrate; and
 - (d) removing the unpolymerized portion of the self-assembled monolayer(s).
- 20 18. The method according to claim 17 further comprising (e) etching of the surface of the substrate.
 - 19. The method according to claim 17 further comprising (e) deposition of an inorganic or organic material onto the substrate.
- 25 20. In a method of photolithography wherein the improvement comprises the use of a resist comprising at least one polymeric self-assembled monolayer.

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2. Synthesis of ω-functionalized, diacetylenic n-alkanethiols, a, I equiv of 1.5 M MeLi/LiBr, THF, -78 °C; BritingCH₂OMOM/HMPA; KF/DMF, π, b, I equiv of 1.6 M BuLi, THF, 0 °C; 5 equiv of Br(CH₂)₁₀Br/HMPA, π, c, conc. CI/M OH, π, d, excess PDC/DMF, π, e, 6 equiv of NaSH/EtOH, 50-55 °C, 4-8 h, sonicated. MOM = CH₂OCH₃: n = 2, 10.

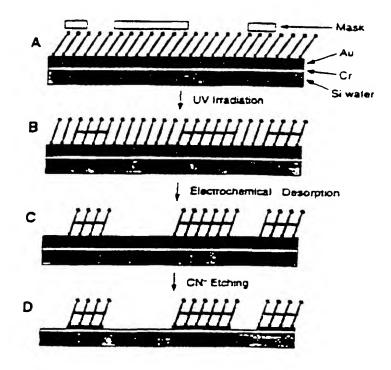
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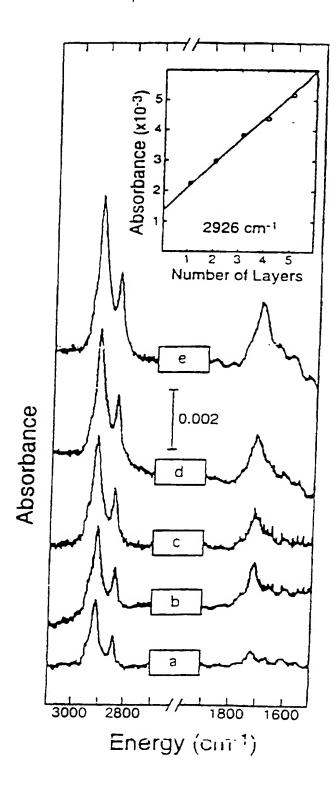
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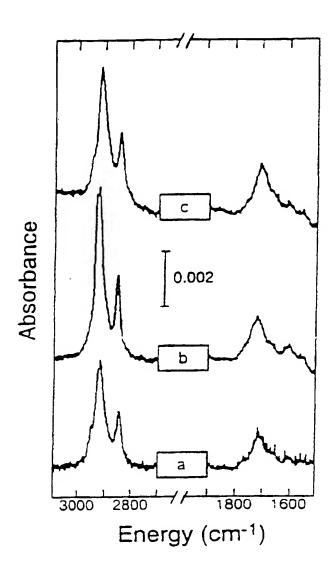
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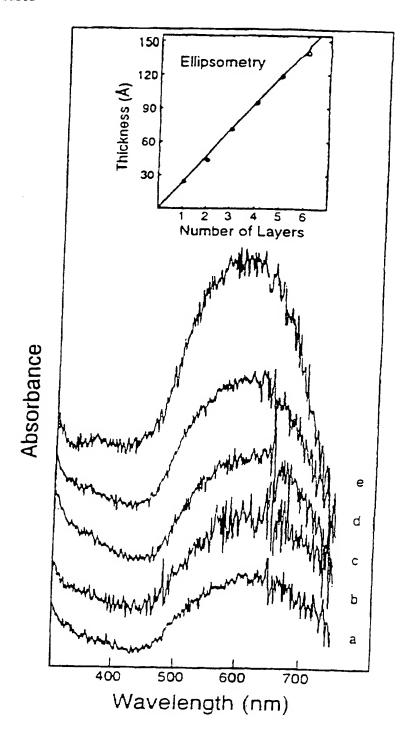
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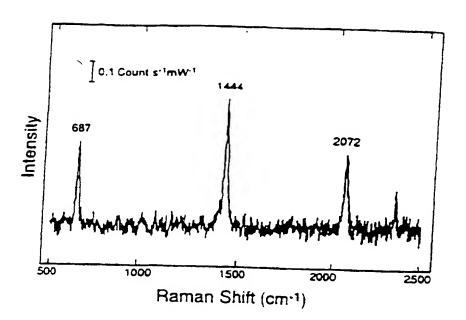
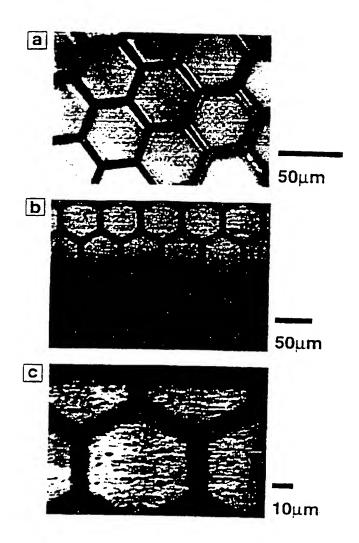
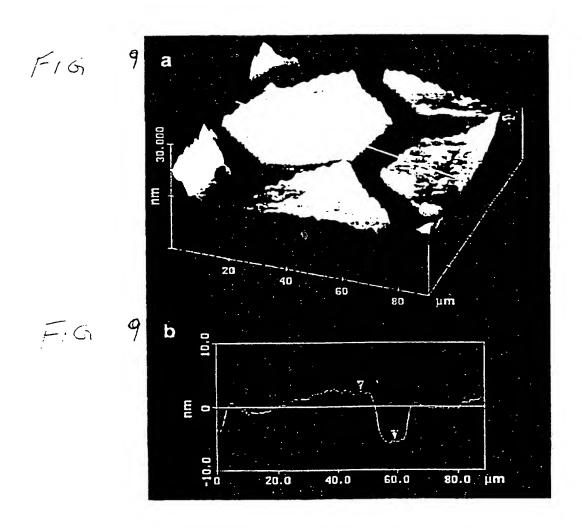


FIG 7



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INTERNATIONAL SEARCH REPORT

International application No. PCT/US97/06076

IPC(6) US CL	SSIFICATION OF SUBJECT MATTER :B05D 5/10, 3/06; G03F 7/025, 7/075 : 156/272.2; 427/,333,337; 430/325,328					
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C. DOC	CUMENTS CONSIDERED TO BE RELEVANT					
Category*	Citation of document, with indication, where a	appropriate, of the relevant passages	Relevant to claim No.			
×	ITOH. M. et al. Preparation Dimensional Polymer Films by Cl Alkanethiol Self-Assembled Mor Copper against Corrosion.J.Ele 1995. Vol. 142. No. 11. page equation 4.	hemical Modification of an nolayer for Protection of ectrochem.Soc. November	1,2,6-9,13-16			
X Y	US 5338571 A (MIRKIN et al) 16 44-48, figures 2A,3,4.	August 1994, col. 3, lines	1,2,7,8 13,16			
X Y	US 4,539,061 A (SAGIV) 03 Se lines 39-68, column 4, lines 45-6 claim 2, column 6, lines 14-45.		1-12 13-20			
X Furth	er documents are listed in the continuation of Box (C. See patent family annex.				
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INTERNATIONAL SEARCH REPORT

International application No.
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C (Continua	tion). DOCUMENTS CONSIDERED TO BE RELEVANT	
Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
Y	KIM.T. et al. Polymeric Self-Assembling Monolayers.1. Tetrahedron Letters. 1994. Vol.35. No. 51. pages 9501-9504, especially page 9502.	1-20
A	KIM.T. et al. Polymeric Self-Assembled Monolayers.2. J.Am.Chem.Soc. 1995. Vol. 117. pages 3963-3967.	1-16
A	BATCHELDER.D.N. et al. Self-Assembled Monolayers containing Polydiacetylenes. J.Am.Chem.Soc. 1994. Vol. 116. pages 1050-1053, especially page 1050.	1-20

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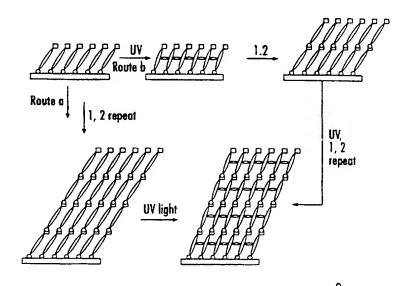
With international search report.

Before the expiration of the time limit for amending the claims and to be republished in the event of the receipt of amendments.

(54) Title: POLYMERIC SELF-ASSEMBLED MONO- AND MULTILAYERS AND THEIR USE IN PHOTOLITHOGRAPHY

(57) Abstract

A self-assembled multilayer and in particular polymeric self-assembled multilayer can be effectively produced from two or more selfassembled monolayers on a substrate where each of the self-assembled monolayers is produced for a block containing a first functional group and a second functional group where the second functional group is reacted with the first functional group. The production of polymerizable, self-assembled mono- and multilayers from, e.g., blocs containing at least two acetylene groups and/or polymerizable end groups, is also provided. The polymerized mono- or multilayer can be employed in a variety of applications including photolithography.



1. SOCI₂; 2. $HS(CH_2)_{10}C \equiv CC \equiv C(CH_2)_{10}COOH/CHCl_3;$ 3. ⊕ ≡ (()

^{* (}Referred to in PCT Crazette No. 53/1977, Section II)

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TITLE OF THE INVENTION

Polymeric Self-Assembled Mono- and Multilayers and Their Use in Photolithography

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Field of the Invention

The present invention relates to self-assembled monoand multilayers and, in particular, polymeric selfassembled mono- and multilayers as well as the use of self-assembled mono- and multilayers in certain applications such as photolithography.

Background of the Invention

Self-assembled monolayers (SAMs) are known in the art. See, for example, Dubois et al., Annu. Rev. Phys.

- 15 Chem., 1992, 43, p. 437 et seq., which is incorporated herein by reference. Recently, one class of SAM that has received considerable attention are organomercaptans. See, for example, Kim et al. "Polymeric Self-Assembling Monolayer. 1. Synthesis and Characterization of ω -
- Punctionalized N-Alkanethiol Containing a Conjugated Diacetylene Group" Tetrahedron Letters, Vol. , No. 51, pp. 9501-9504, 1994; Kim et al., "Polymeric Self-Assembling Monolayer. 2. Synthesis and Characterization of Self-Assembled Polydiacetylene Mono- and
- Multilayers.", J. Am. Chem. Soc., 1995, 117, pp. 3963-3967; and Batchelder et al., "Self-Assembled Monolayer containing Polydiacetylenes", J. Am. Chem. Sc., 1994, 116, pp. 1050-1053, each of which are incorporated herein by reference in their entirety.
- One area of study relating to SAMs has involved the stability of such monolayers. While in certain environments, e.g., water or air at room temperature, the SAM's can be considered robust, one disadvantage associated with the use of most SAMs relates to their

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fragility in environments that involve elevated temperatures and/or solvents able to penetrate the SAM.

One solution to this problem is represented by the polymerization of SAMs. Batchelder et al disclose the use of UV radiation in polymerizing SAMs produced from methyl-terminated diacetylene disulfide. While it has been found that polymerized SAMs have high structural integrity and are more rugged than their unpolymerized counterparts, SAMs produced from methyl-terminated diacetylene disulfide are very limited in their use. Because of the presence of the methyl group at the terminal end of the SAM blocks, the surface of the SAM according to Batchelder is considered nonreactive.

In a different vein, the art has looked at

multilayer assemblies of self-assembling monolayers. For example, the formation of built up films by the stepwise adsorption of individual monolayers is described in U.S. Patent No. 4,539,061 to Sagiv. However, these monolayers suffer from the same disadvantages as other non-polymerized monolayers. Moreover, the process described in this patent itself is limiting. That is, the process requires the use of a molecule having a polar "head" and a non-polar functional group in producing the monolayer. This is followed by a conversion of non-polar groups to a polar head in order to allow for the build up of subsequent monolayers. Accordingly, not only is the disclosed process relatively complex but the practical

Accordingly, the need still exists for an improved 30 polymeric self-assembled mono- and multi-layer structure that does not suffer from the limitations associated with previous films.

applications are limited.

Summary of the Invention

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Surprisingly, it has been found that certain self-assembled monolayers are capable of being formed into self-assembled multilayers, and, in particular, polymeric self-assembled multilayers. Moreover, the polymeric self-assembled mono- and multi-layers described herein have a combination of properties which allows them to be employed in a wide variety of applications such as adhesion layers and lithographic resists.

In one aspect the present invention relates to a self-assembled multi-layer structure comprising a substrate and a plurality of self-assembled monolayers, with each of said self-assembled monolayers being produced from a block containing a first functional group and a second functional group reacted with the first functional group. In one particular preferred embodiment, the first functional group is a thiol group, the second functional group is a carboxylic acid group, hydroxyl group or an epoxy group. Moreover, at least one of the self-assembled monolayers are polymerized, e.g., produced from a compound containing at least one pair of conjugated acetylene bonds and/or a polymerizable end group and then polymerized.

In another aspect of the invention, a method of photolithography is provided. This method includes

25 providing a support having at least one self-assembled monolayer thereon, said self-assembled monolayers produced from a molecule including at least two acetylene bonds, introducing a mask onto self-assembled monolayer in a desired pattern inducing the polymerization of the unmasked regions of the self-assembled in a plane roughly parallel to the substrate in removing the unpolymerized portion of the self-assembled monolayers. The method can further include

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etching of the substrate surface subsequent thereto or deposition of an inorganic or organic material thereon.

Brief Description of the Drawing

Figure 1 illustrates a synthesis method for producing diacetylenic thiols which can be employed in the present invention;

Figure 2 illustrates a method for forming a polymeric self-assembled mono- or multilayer;

Figure 3 illustrates a method of photolithography 10 according to the present invention;

Figures 4-7 illustrate properties of polymeric multilayers;

Figure 8 are micrographs relating to the exemplified method of photolithography; and

15 Figure 9a is a three dimensional STM image of a pattern Au surface and Figure 9b is a depth profile on the line of Figure 9a.

Description of the Preferred Embodiments

The self-assembled monolayers employed in the
20 present invention are produced from molecules or blocks
that include at least two functional groups, i.e., a
first functional group capable of being attached to a
surface, and a second functional group which is capable
of being covalently bonded with the first functional
25 group of another molecule or block. The use of blocks

25 group of another molecule or block. The use of blocks having such a combination of functional groups allows for the sequential buildup of monolayers on a surface.

Examples of suitable first functional groups include thiol groups, carboxylic acids and silanes, with thiols being preferred.

The selection of suitable second functional groups is dependent, of course, on the first functional group employed. For example, preferred second functional groups for use where the first functional group is a

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thiol include carboxylic acid groups, hydroxy groups, and epoxy groups.

As discussed above, it is also desirable that the SAM be polymerizable. While the various applications associated with the present invention can utilize SAMs polymerized by any known technique, the following two methods are discussed herein.

In one embodiment for providing a polymerizable SAM, it is desired that the self-assembled monolayers be produced from molecule or blocks containing at least one pair of conjugated acetylene bonds. While the conjugated bonds can be placed at any suitable location in the block, near or at the center of the molecule is preferred. By center it is meant that there are about the same number of carbon atoms on both sides of the conjugated bonds. SAMs produced from such blocks are typically polymerized by irradiation, e.g., UV, visible light, infrared, x-rays, and the like with UV irradiation being preferred.

Another method of providing a polymerizable SAM involves the use of polymerizable second functional or end groups. Examples of such groups, which can be polymerized through irradiation or electrochemistry, include aniline groups, thiophene groups and pyrrole groups.

Combinations of the foregoing could also be employed. For example, a multi-layer including one or more monolayers produced from blocks with conjugated acetylene bonds and one or more layers produced from compounds having polymerizable end groups. Moreover, blocks containing both conjugated acetylenic groups and polymerizable end groups can be employed.

The use of SAMs produced from conjugated acetylene bonds is preferred due to the fact that the polymerization

Water A. C. and John Same

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of SAMs with polymerizable end groups results in a material that is not further reactive. That is, by polymerizing the end groups further reaction of the SAM is not possible.

Preferred examples of suitable blocks for forming the monolayers include organomercaptans such as diacetylenic thiols, e.g., ω-functionalized n-alkanethiols. The compounds preferably have from 4-40 carbon atoms, more preferably 20-30, and still more preferably about 25 carbon atoms. Specific examples of suitable compounds include ω-functionalized n-alkanethiols containing a diacetylene group such as HS(CH₂)₁₀C≡CC≡C(CH₂)₁₀COOH and HS(CH₂)₁₀C≡CC≡C(CH₂)₁₀OH.

Methods for producing SAMs in which the desired

15 functional groups disclosed in the two Kim et al.

articles discussed above and thus need not be described
in detail here. However, for sake of completeness,
Figure 1 illustrates a suitable synthesis technique. As
illustrated in this figure, the synthesis of diacetylene
20 containing alkanethiols includes the selective
deprotection of 1,4-bis(trimethylsilyl)-1,3-butadiyne (1
of Fig. 1), subsequent reaction with primary
alkylbromides and deprotection of the remaining
trimethylsilyl group. The lithium diacetylenide (2 of

25 Figure 1) can then be reacted with 1,10-dibromodecane to
give a functionalized alkylbromide (3 of Figure 1).
Oxidation of the alkylbromide provided a diacetylene (5
of Figure 1) that is then converted to the corresponding

Where conjugated acetylenic bonds are employed, polymerization of the SAMs in a plane which is roughly parallel to the surface of the substrate can be performed through irradiation with, e.g., visible light, infrared, x-ray or UV radiation, with UV being preferred. See, for example, the discussion in the two Kim et al. articles

thiols (6,7 of Figure 1).

and the Batchelder et al. article. As discussed above, the use of polymerizable end groups allows for polymerization through electrochemical techniques that are also recognized in the art.

Multilayers assemblies of self-assembled monolayers are produced through the sequential deposition of a plurality of SAMs (Figure 2).

In particular, the individual monolayers are covalently bonded to the immediate preceding layer

10 through the reaction of the second functional group of a first block with the first functional group of a second block. For example, where the second functional group is a carboxylic acid and the first functional group is a thiol, the acid is converted to an acid chloride and the layers are then covalently bonded through a thioester linkage. The conditions associated with such processes would be well within the purview of those skilled in the art.

Moreover, other suitable combinations of 20 functional groups capable of providing a covalent bond between the individual layers would also become apparent to hose skilled in the art and can also be employed.

Polymeric multilayers according to the present invention are preferably produced by either of two synthesis routes illustrated in Figure 2. Although the following discussion with focus on the preferred use of the carboxylic acid-terminated alkanethiol diacetylene $HS(CH_2)_{10}C\equiv CC\equiv C(CH_2)_{10}COOH$, it should not be limited to that particular molecule.

In general, synthesis Route a illustrates the ability to provide an assembled multilayer in which the assembly of individual monolayers is provided and are polymerized during production of the multilayer but, which subsequent to polymerization, each layer is polymerized.

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Alternatively, Route b illustrates a synthesis method by which each layer is polymerized as it is introduced onto the previous layer.

As can be seen, both routes involve the same

5 process for introducing the SAM onto the substrate or the
previous SAM layer, i.e., converting the carboxylic acid
terminal groups to an acid chloride by exposure to SOCl₂
vapor followed by subsequent reaction with the desired
block. The significant difference between the two routes

10 is the timing of the irradiation, i.e., either once after
depositing all of the SAMs or after the deposition of
each SAM.

The present invention is therefore capable of providing an arrangement exists where all of the layers are polymerized or, where one or more of the outermost layers may not be polymerized with the balance of the layers being polymerized.

Surprisingly, not only are the polymerized SAMs are extremely rugged, they are better barriers to 20 transfilm mass transfer than unpolymerized monolayers. Accordingly, it has been discovered that the selfassembled mono- and multilayers according to the present invention can be employed as an adhesion layer in a variety of environments. One such area is as adhesion 25 layers. Adhesion layers are, in general, known in the art and can be employed in a number of different environment. Such layers can allow the formation of composite materials which are otherwise difficult, if not impossible, to provide. For example, merely introducing 30 a layer of gold onto silicon is ineffective due to poor compatibility, and the gold will peel off in a matter of days. On the other hand, through the use of a suitable adhesion layer, e.g., chromium, which is capable of bonding to both the gold and the silicon, suitable 35 composites can be provided.

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Here, self-assembled mono- and multilayers and in particular, polymerized mono- and multilayers according to the present invention can be employed as adhesion layers in a variety of environments. First of all, the ability of SAMs to bond to a variety of substrates under a wide range of conditions, e.g., temperatures less than about 400 C, makes their use attractive in this context. Moreover, as discussed above, once polymerized, the SAMs are stronger, more resistant to degradation, and thus,

Specific examples of suitable substrates include gold, aluminum, aluminum oxide, gallium-arsenide, copper and silver.

Moreover, upon introduction of a self-assembled

15 mono- or multilayer onto a substrate, additional outer
layers can be provided. Such additional layers are
limited only by their ability to react with the second
functional group of the SAM and the intended final use
for the composites. Specific examples of such "outer

20 layers" include chemically sensitive organic and
inorganic materials, metals and semiconductors to name a

The multilayer assemblies according to the present invention are capable of providing additional advantages.

In this regard, a polymerized multilayer provides a highly structured three-dimensional, surface-confined polymer which can be employed as, e.g., ordered conductive polymers, third-order nonlinear optical materials and, one particularly preferred embodiment, lithographic resists.

A method for using self-assembled mono- and multilayers as a photoresist and, in particular, a negative photoresist, is illustrated by Figure 3.

This aspect of the invention involves the use of a 35 self assembled mon- or multilayer and the introduction of

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a suitable mask in a desired pattern onto the surface of the mono- or multilayer. The self-assembled monolayer is then irradiated with UV radiation, so as to induce polymerization in the unmasked regions of the mono- or multi-layer.

The unpolymerized portion of the resist is then selectively desorbed using a suitable electrochemical reductive stripping method which results in a negative image of the mask. Selective stripping can be effectively employed in this process because the polymeric mono- or multilayers are sufficiently insoluble in the stripping agent and strongly bond to the surface that only the monomeric SAMs are removed. Finally, suitable processing, e.g., etching can be preformed to elaborate on the negative image of the mask in providing the desired resist. Alternatively, this can involve deposition of an inorganic or organic material thereon.

The individual steps discussed above, e.g., selective stripping, etching, depositions and the like, 20 can be performed with traditional materials and by traditional techniques. In fact, the ability to readily and easily "plug" the resists of the present invention into existing processes without the costs in both time and money associated with retrofitting or redesigning is 25 a significant advantage of the inventive process.

Moreover, because the use of self-assembled monoor multilayer consist of single small molecules or very thin layers of molecules, the theoretical resolution of lithography is the graphically defined features can be as 30 small as a few (e.g., less than 10) nanometers when patterned by an appropriate tool, e.g., the tip of scanning tunnel microscope.

SAMs are extremely dense and, in some cases the structure approaches that of a two-dimensional crystal.

This ensures high effective density and simplifies resist

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application and stripping. In fact, the use of stripping solutions can be greatly minimized or eliminated. The environmental impact of that advantage in terms of eliminating the need to process or dispose such solution 5 can not be understated.

Finally, insofar as the terminal group, i.e., second functional group, of the SAMs can be varied, selective chemicals physical vapor definition of materials can be enhanced.

The present invention will now be described in terms of certain preferred examples thereof. However, these examples are intended to be illustrative in nature and should, in no way, limit the present invention.

Example 1

Gold substrates for FTIR-external reflectance spectroscopy (FTIR-ERS), ellipsometry, and Raman spectroscopy were prepared by thermal evaporation of 2000 Å of Au over a 50-Å Cr adhesion layer confined to Si(100). For UV-vis measurements, transparent substrates were prepared by thermal deposition of 50 Å of Au onto a (3-mercaptopropyl)trimethoxysilane adhesion layer confined to a quartz substrate. The substrates were cleaned in piranha solution (30% H₂O₂:concentrated H₂SO₄ = 1:3)

Monolayers were prepared by soaking the substrate in a 1 mM CHCl₃ solution of HS(CH₂)₁₀C=CC=C(CH₂)₁₀COOH for 1 h, removing the substrate, and then rinsing it in acetone and deionized water. Multilayers were prepared by thioester coupling of HS(CH₂)₁₀C=CC=C(CH₂)₁₀COOH to the base 30 monolayer either before or after polymerization of the base layer. The carboxylic acid-terminated SAM was positioned in a closed container, and after the container was purged with dry N₂ for 5 min, SOCl₂ vapor was introduced for 10 min. Control experiments, which

involved monitoring this reaction by FTIR-external reflectance spectroscopy in real time, indicated that the absorbance due to the carboxylic acid carbonyl stretching mode originally present around 1713 cm⁻¹ was completely eliminated within 1 min and replaced by an absorbance at 1813 cm⁻¹ that we identify as the acid chloride carbonyl mode. The substrate was then transferred to a 1 mM CHCl₃ solution of HS(CH₂)₁₀C=CC=C(CH₂)₁₀COOH, and thioester formation was complete with 1 h. Subsequent layers were prepared similarly.

Except for the UV-vis spectroscopic experiments, polymerization was performed by placing the substrate into a gas-tight container and irradiating it under a N_2 purge for 5 min with a lamp (Oriel, Model 6035) 15 positioned 1 cm above the substrate.

FTIR-ERS measurements were made using a Digilab FTS-40 FTIR spectrometer equipped with a Harrick Scientific Seagull reflection accessory and a liquid N_2 -cooled MCT detector. All spectra were obtained using p-20 polarized light incident on the Au substrate at an angle of 84°.

Thickness measurements of the unpolymerized monoand multi-layers were made using a Gaertner Scientific ellipsometer (Model L116C). The data were obtained using 25 the 488 nm Ar laser line, but the 633 nm He-Ne laser line yielded similar results. A refractive index of 1.46 was assumed for the thickness calculations. Due to optical absorptions it was not possible to measure the thickness of the polymerized multilayer SAMs using ellipsometry.

The UV-vis spectra were recorded on a Hewlett-Packard diode-array spectrometer by first obtaining a background spectrum of a four-layer, unpolymerized film, and then polymerizing it for various lengths of time without removing the substrate from the spectrometer (in these experiments the UV light was maintained 0.5-1.0 cm

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away from the substrate). Throughout these experiments the substrate was kept under a N_2 purge.

The Raman measurement system consists of a Kr-ion laser (Model Innova 90K, Coherent Laser Group, Santa 5 Clara, CA), a 3-in.-diameter holographic notch filter (Model Notch-Plus, Kaiser Optical System, Ann Arbor, MI), 0.5-m single-grating Czerny-Turner spectrograph (Model 500M, SPEX Industries, Edison, NJ), a liquid- N_2 -cooled 1024-by-26-pixel charge-coupled device (CCD) (Model CCD-10 1000LF, SPEX Industries). Laser power was measured by a semiconductor detector (Model 840-C and 818-SL/CM, Newport, Irvine, CA). The spectral position, of the horizontal CCD pixels were calibrated using emission lines of known wavelengths from a Ne lamp (Model AlA/NE-15 2, Chicago Miniature Lamp, Buffalo, IL). conditions for Raman scattering were 5 mW 647.1 nm excitation 200 mm slit width (equivalent to 6.7 cm⁻¹ band pass), and 5 s integration time. The spectra were corrected for a slowly varying spectral background using 20 set points more than 200 cm⁻¹ apart. The laser was

focused to a point on the sample surface using a $f=250~\mathrm{mm}$ spherical focusing lens.

Figure 4 shows FTIR-ERS spectra of

HS(CH₂)₁₀C≡CC≡C(CH₂)₁₀COOH obtained after each of five

25 incremental increases in layer thickness and subsequent polymerization immediately following the addition of each layer (Route b). Figure 4-a corresponds to a single, polymerized monolayer of HS(CH₂)₁₀C≡CC≡C(CH₂)₁₀COOH. The spectrum is composed of three prominent peaks: methylene asymmetric and symmetric C-H stretches at 2926 and 2854 cm⁻¹, respectively, and the carboxylic acid CDO stretch at 1713 cm⁻¹. The positions of the methylene bands are in general agreement with previous studies, and they indicate that the hydrocarbon portions of the chains

35 probably exist in a liquid-like state. As discussed

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later, the absorbance of the methylene bands in the second and subsequent layers is greatly attenuated following polymerization due to a change in orientation of the hydrocarbon backbone relative to the Au substrate.

After obtaining the spectrum in Figure 4a, we 5 reacted the terminal acid groups with SOCl, to convert them to the acid chloride, which reacts with $HS(CH_2)_{10}C = CC = C(CH_2)_{10}COOH$ to form a thioester-bound bilayer. Exposure to UV light polymerizes the second 10 layer. Figure 4b shows that this treatment increases the absorbance due to both the methylene and carbonyl groups. The methylene band intensity increased by about 30% which is consistent with subsequent layering steps (Figure 4c, d, e), which show the same incremental increase in 15 absorbance observed for the second layer (inset of Figure 4). From these data we conclude that the first polymerized layer is significantly tilted with respect to the surface normal, perhaps as much as 35° based on the ellipsometric data discussed later, but subsequent 20 polymerized layers are oriented more perpendicular to the surface-perhaps about 20° from the surface normal based on ellipsometry data and the difference in the maximum IR absorbance.

The change in orientation of the hydrocarbon

25 backbone upon polymerization is confirmed by Figure 5.

Figure 5a, which is the same as Figure 4c, is a spectrum of a three-layer polydiacetylene film. Figure 5b is the spectrum that results from coupling a fourth unpolymerized layer to the multilayer of Figure 5a. The large change in absorbance in the hydrocarbon region is consistent with the addition of the fourth layer.

However, upon polymerization (Figure 5c) the magnitude of these peaks decreases significantly. This result suggests that the methylene bonds are oriented more

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parallel to the substrate after polymerization and confirms the structural change mentioned earlier.

Figure 6 also shows in situ UV-vis transmission spectra as a function of polymerization time for a 4-5 layer film made according to Route a (Figure 2). The data indicate that polymerization is complete within 5 min. Exposure of the film to UV light for times up to 8 min revealed no further change in the intensity or position of the absorption maximum, which occurs at 620 nm. In studies of polydiacetylene Langmuir-Blodgett films, two absorption maxima are usually observed. One is found between 600 and 640 nm, which corresponds to the so-called blue polymer, and the other is between 500 and 550 nm, which corresponds to the shorter or less conjugated red polymer. The self-assembly approach yielded only the more highly conjugated blue polymer.

The surface Raman spectrum of the same substrate used to obtain the data shown in Figure 4 confirms polymerization (Figure 7). Three major peaks located at 20 687, 1444, and 2072 cm⁻¹ all originate from vibrations of the polydiacetylene backbone, which contains conjugated and alternating double and triple bonds. The peak at 687 cm⁻¹ has previously been assigned to a bending mode of the backbone, and peaks at 1444 and 2072 cm⁻¹ correspond 25 mainly to the C=C and C=C stretching vibrations, respectively. These frequencies are significantly lower than those observed for isolated C=C and C=C stretching modes (approximately 1620 and 2260 cm⁻¹, respectively). The decrease in both frequencies is due to extensive electronic delocalization in the backbone of the polymerized diacetylene groups.

Example 2

A diacetylenic SAM was used as a negative photoresist and the image of a transmission electron

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microscope (TEM) minigrid was transferred into a Au substrate using the three steps illustrated in Figure 3.

First, the minigrid was placed in contact with a SAM composed of close-packed $HS-(CH_2)_{10}C\equiv CC\equiv C(CH_2)_{10}COOH$ 5 molecules confined to a Au/Cr/Si surface. The entire assembly was then exposed to UV light, which induced polymerization in the unmasked regions of the SAM (B-Figure 3). Next the unpolymerized portion of the resist was selectively desorbed using an electrochemical 10 reductive stripping method (C-Figure 3). stripping was possible because the polymeric SAM is sufficiently insoluble and strongly bound to the surface through multiple Au/S and van der Waals interactions that it survives potential excursions that remove monomeric 15 organomercaptan SAMs. Resist removal resulted in a negative image of the mask, which can be elaborated by etching the grid image into the Au surface with an Ogsaturated 1 M KOH plus 10 mM KCN aqueous solution (D-Figure 3).

Figure 8a is an optical micrograph of the 400-mesh (holes per linear inch) Cu TEM minigrid, which was used to pattern the Au surface. Panels b and c of Figure 8 are scanning electron micrographs (SEMs) of a patterned Au surface, such as that illustrated in Figure 3, frame D obtained at two different magnifications. At this level of resolution, an excellent reproduction of the mask features was observed.

Figure 9a is a three-dimensional STM image (90 μ m x 90 μ m) of the pattern shown in Figure 7b,c. The 30 grooves in this image are regions of the Au surface that have been etched by the KCN/KOH solution, while the hexagonal regions are those parts of the Au surface that etch at a reduced rate as a result of the presence of the

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polymeric SAM resist. STM depth profiles (Figure 9b) indicate the grooves were about 7-8 nm deep.

Although the present invention has been described in terms of certain preferred embodiments, those skilled 5 in the art will recognize that various modifications, omissions, substitutions, and other changes can be made without departing from the spirit thereof. Thus, the scope of the present invention should be limited only by the scope of the following claims including equivalents 10 thereof.

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What is claimed is:

1. A self-assembled multilayer structure comprising:

a substrate and

- a plurality of self-assembled monolayers deposited thereon, with each of said self-assembled monolayers being produced from a block containing a first functional group, a second functional group that is reactive with the first functional group, wherein at least one of the monolayers is polymerized in a plane roughly parallel to the substrate.
 - 2. The structure according to claim 1 where the first functional group is a thiol, carboxylic acid or silane group.
- 3. The structure according to claim 1 where the second functional group is a carboxylic acid group, hydroxy group, or epoxy group.
- The structure according to claim 1 wherein at least one of the self-assembled monolayers are produced
 from a compound further including at least one pair of conjugated acetylene bonds.
 - 5. The structure according to claim 4 wherein the compounds contains a pair of conjugated acetylene bonds in the center of the compound.
- 25 6. The structure according to claim 1 wherein at least one of the self-assembled monolayers is produced from a compound having a second functional group which is polymerizable.

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- 7. The structure according to claim 1 wherein more than one of the self-assembled monolayers are polymerized in a plane roughly parallel to the substrate.
- 8. The structure according to claim 1 wherein each of the self-assembled monolayers are polymerized in a plane parallel to the substrate.
 - 9. The structure according to claim 4 wherein the self-assembled monolayers are produced from organomercaptans.
- 10 10. In the structure according to claim 8 wherein the organomercaptans are diacetylenic thiols.
 - 11. The structure according to claim 8 wherein the organomercaptans are ω -functionalized diacetylenic nalkanethiol having 4-40 carbon atoms.
- 15 12. The structure according to claim 10 wherein the diacetylenic thiol has the formula $\text{HS}(\text{CH}_2)_{10}\text{C}\equiv\text{CC}\equiv\text{C}(\text{CH}_2)_{10}\text{COOH or HS}(\text{CH}_2)_{10}\text{C}\equiv\text{CC}\equiv\text{C}(\text{CH}_2)_{10}\text{OH}.$
 - 13. A multilayer structure comprising:
 a substrate;
- an adhesion layer comprising at least one selfassembled monolayer bonded thereto; and at least one outer layer bonded to said adhesion layer, wherein said at least one outer layer is not compatible with said substrate.
- 25 14. The structure according to claim 13 wherein at least a portion of at least one of the self assembled monolayers is polymerized in a plane roughly parallel to the substrate.

- 15. The structure according to claim 13 wherein at least one adhesion layer comprises a self-assembled monolayer which is polymerized in a plane roughly parallel to the substrate.
- 5 16. The structure according to claim 13 further comprises one or more additional layers between the substrate and the adhesion layer.
 - 17. A method for photolithography comprising:
- (a) providing a support having at least one self-10 assembled monolayer, said self-assembled monolayer being produced from a molecule including at least two acetylene bonds;
 - (b) introducing a mask onto said self-assembled monolayer in a desired pattern;
- 15 (c) inducing the polymerization of the unmasked regions of the self-assembled monolayer in a plane parallel to the substrate; and
 - (d) removing the unpolymerized portion of the self-assembled monolayer(s).
- 20 18. The method according to claim 17 further comprising (e) etching of the surface of the substrate.
 - 19. The method according to claim 17 further comprising (e) deposition of an inorganic or organic material onto the substrate.
- 20. In a method of photolithography wherein the improvement comprises the use of a resist comprising at least one polymeric self-assembled monolayer.

INTERNATIONS SHOWS PART A.

a. 1 equiv of 1.5 M MeLI/LIBr, THF, -78 °C; Br(CH₂),CH₂OMOM/HMPA; KF/DMF, rt. b. 1 equiv of 1.6 M BuLI, THF, 0 °C; 5 equiv of Br(CH₂)₁₀Br/HMPA. rt. c. conc. HC1/MeOH, rt.

6 equiv of NaSH/EtOH, 50-55 °C, 4-8 h, sonicated. MOM=CH2OCH;; n=2,10.

d. excess PDC/DMF, rt.

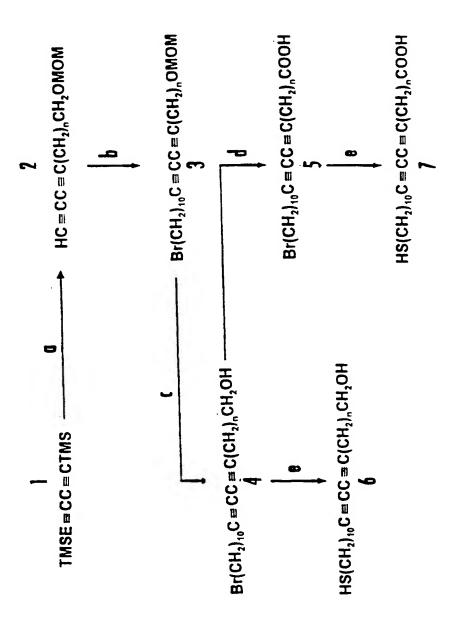
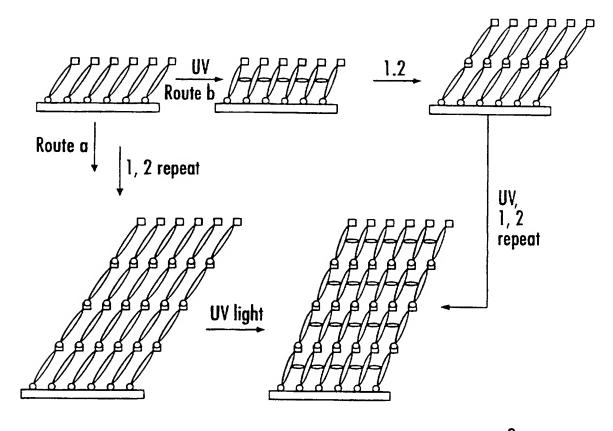


FIG. 1

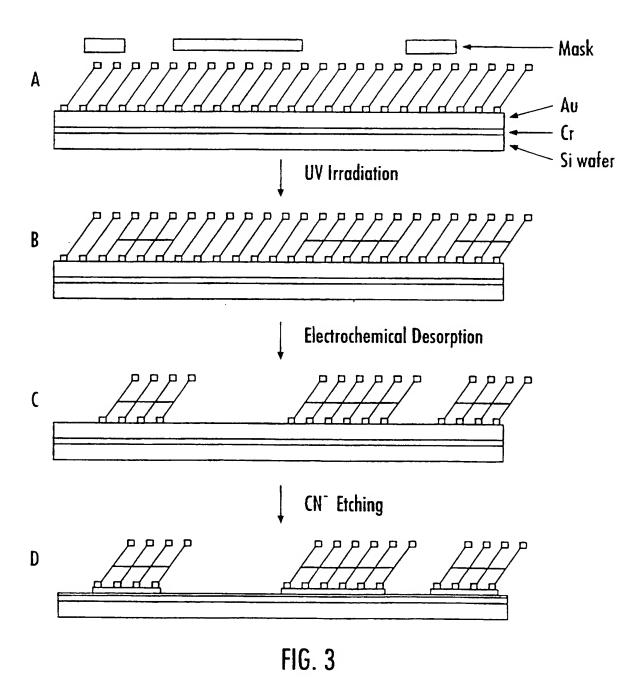


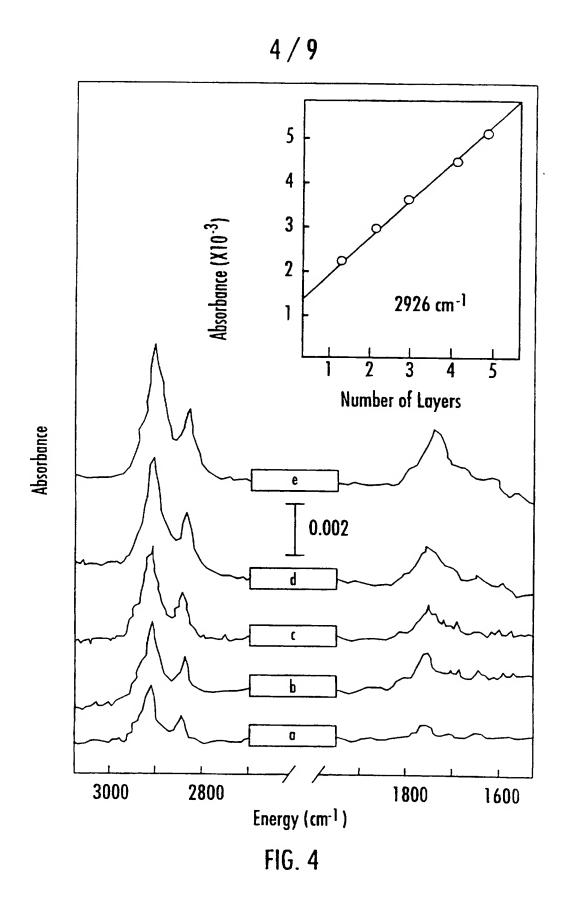
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$$SOCI_2$$
; 2. $HS(CH_2)_{10}C = CC = C(CH_2)_{10}COOH/CHCI_3$; 3. $\triangle = CCI$

4.
$$\triangle \equiv CS$$
; 5. $\triangle \equiv HS(CH_2)_{10}C \equiv CC \equiv C(CH_2)_{10}COOH$;

FIG. 2

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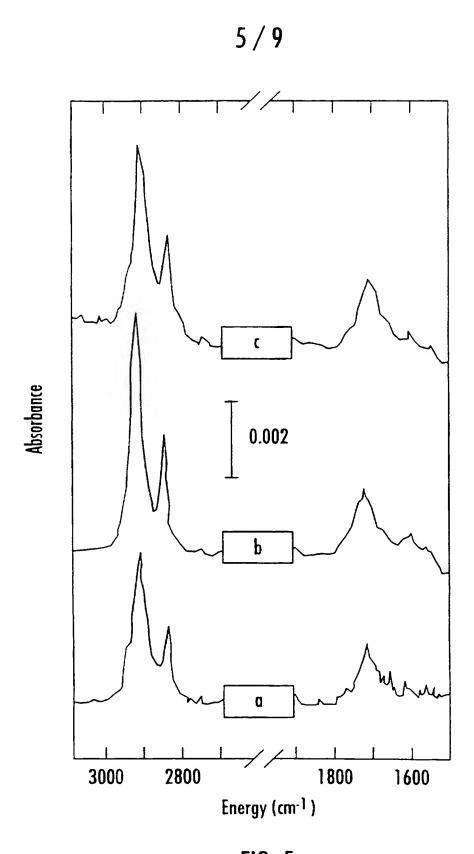
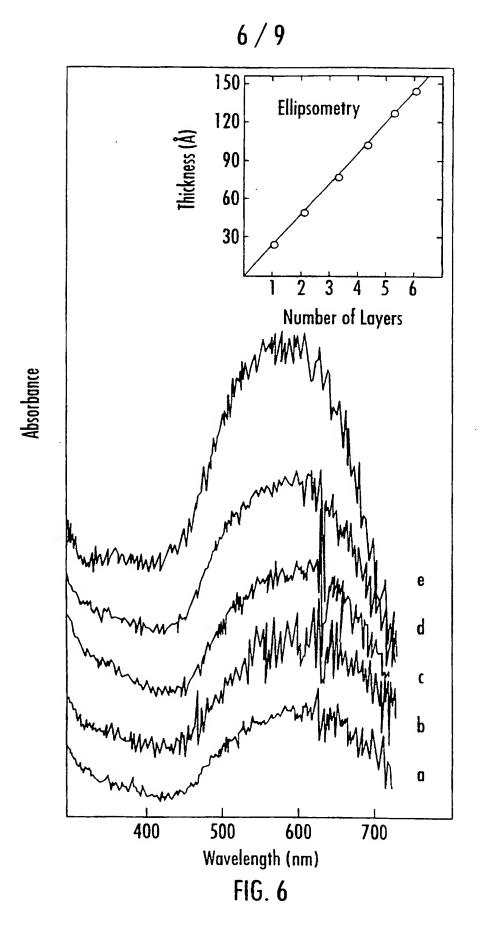
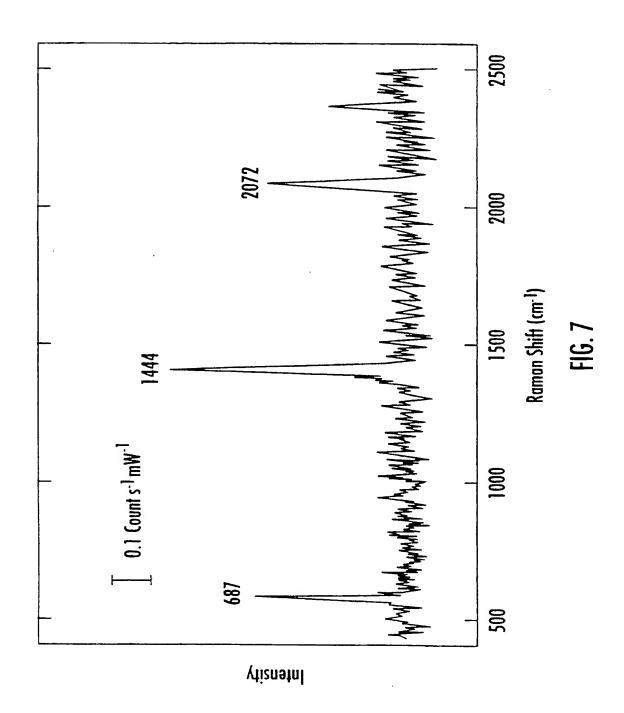


FIG. 5
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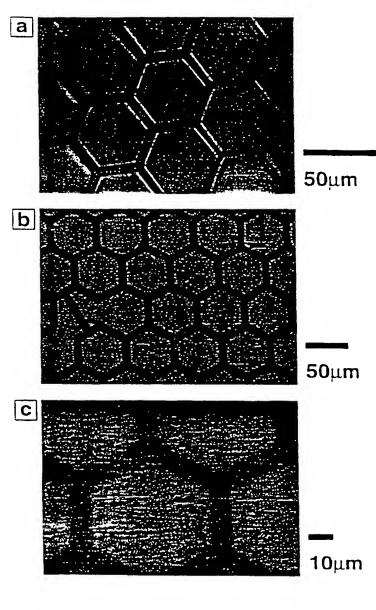


FIG. 8

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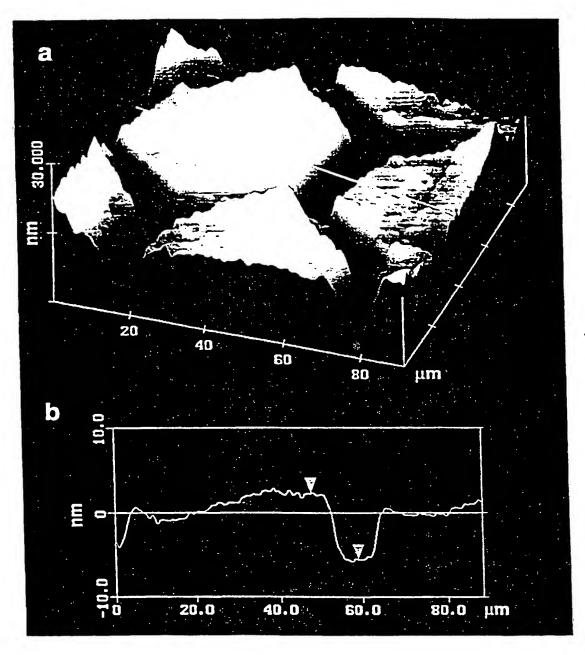


FIG. 9

INTERNATIONAL SEARCH REPORT

International application No. PCT/US97/06076

IPC(6) US CL	SSIFICATION OF SUBJECT MATTER: :B05D 5/10, 3/06; G03F 7/025, 7/075 : 156/272.2; 427/,333,337; 430/325,328 to International Patent Classification (IPC) or to both	th national classification as	nd IPC	
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Minimum d	ocumentation searched (classification system follow	ed by classification symbol	ols)	
U.S. ;	156/272.2; 427/,333,337; 430/325,328			
Documenta	tion searched other than minimum documentation to t	he extent that such docume	ents are included	I in the fields searched
Electronic o	ata base consulted during the international search (name of data base and, wi	here practicable	, search terms used)
APS, CA search to	PLUS erms: self assembl?, monolayer#, thiol#, carb	oxylic acid#, silane#, p	oolymeriz?, acc	etylen?
C. DOC	UMENTS CONSIDERED TO BE RELEVANT			
Category*	Citation of document, with indication, where	appropriate, of the relevan	nt passages	Relevant to claim No.
×	ITOH. M. et al. Preparation and Evaluation of Two Dimensional Polymer Films by Chemical Modification of an Alkanethiol Self-Assembled Monolayer for Protection of Copper against Corrosion. J. Electrochem. Soc. November 1995. Vol. 142. No. 11. pages 3696-3703, especially equation 4.			1,2,6-9,13-16
× Y	US 5338571 A (MIRKIN et al) 16 August 1994, col. 3, lines 44-48, figures 2A,3,4.		1,2,7,8 13,16	
X Y	US 4,539,061 A (SAGIV) 03 Selines 39-68, column 4, lines 45-6 claim 2, column 6, lines 14-45.	ptember 1985, c 88, column 5, line	column 3, es 17-22,	1-12 13-20
X Furthe	er documents are listed in the continuation of Roy (See patent fo		
Special categories of cited documents: T leter document published after the international filing date or priority				
As document defining the general state of the art which is not considered to be of particular relevance and not in conflict with the application but cited to understand the principle or theory underlying the invention cannot be considered novel or cannot be considered novel or cannot be considered to involve an inventive step when the document which may throw doubts on priority claim(s) or which is				
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INTERNATIONAL SEARCH REPORT

International application No.
PCT/US97/06076

Category*	Citation of document, with indication when a second of the selection	Relevant to claim No
Category	Citation of document, with indication, where appropriate, of the relevant passages	Kerearu to cuitu No
Y	KIM.T. et al. Polymeric Self-Assembling Monolayers.1. Tetrahedron Letters. 1994. Vol.35. No. 51. pages 9501-9504, especially page 9502.	1-20
A.	KIM.T. et al. Polymeric Self-Assembled Monolayers.2. J.Am.Chem.Soc. 1995. Vol. 117. pages 3963-3967.	1-16
A .	BATCHELDER.D.N. et al. Self-Assembled Monolayers containing Polydiacetylenes. J.Am.Chem.Soc. 1994. Vol. 116. pages 1050-1053, especially page 1050.	1-20
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